

1. Scope :

This specification applies to PN silicon photodiode chips,
Device No. PD-73114U.

2. Structure :

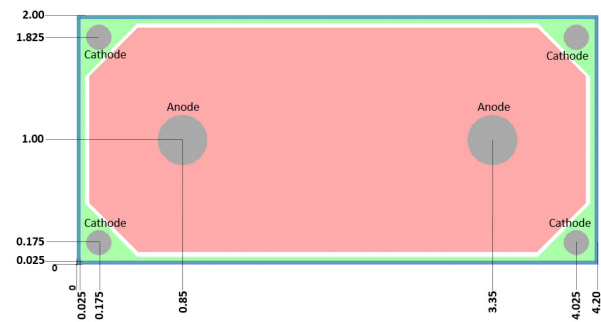
- 2-1. Type : PN diode.
- 2-2. Electrodes :
Top side : SnAu.
Back side : Nitride.

3. Size :

- 3-1. Chip size (including scribe line) : 165.06mils x 78.60mils (4.20mm x 2.00mm)
- 3-2. Real chip size : 163.09 ± 0.79 mils x 76.64 ± 0.79 mils (4.15 ± 0.02 mm x 1.95 ± 0.02 mm).
- 3-3. Chip thickness : 5.90 ± 0.59 mils (0.15 mm ± 0.015 mm)
- 3-4. Active area : 148.55mils x 68.78mils (3.78mm x 1.75mm).
- 3-5. Bonding pad (Anode) : 15.72 mils ± 0.39 mils (0.40 mm ± 0.01 mm) diameter.
- 3-6. Bonding pad (Cathode) : 7.86 mils ± 0.39 mils (0.20 mm ± 0.01 mm) diameter.
- 3-7. The distance between dual bonding pad: 98.25mils (2.5 mm).
- 3-8. Pattern drawing : refer to the attached drawing

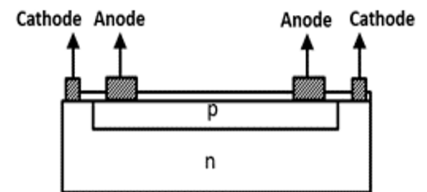
4. Absolute maximum rating (Ta = 25°C):

Parameter	Symbol	Rating	Unit
Reverse Voltage	VR	30	V
Operating temperature	Topr	-40~+85	°C
Storage temperature	Tstg	-40~+125	°C



5. Electro-optical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
*Reverse dark Current	ID	VR=20V Ee=0mW/cm ²			15	nA
*Reverse breakdown voltage	V(BR)R	IR=100uA Ee=0mW/cm ²	60			V
*Forward Voltage_wafer level	VF	IF=20mA Ee=0mW/cm Wafer level			1.2	V



*Based on 100% probing test.

*Pattern drawing: The bottom left corner (including scribe line) is coordinate (0,0) and size unit is mm.